

## Features

- Low drain-source on-resistance:  $R_{DS(ON)}=0.053\Omega(\text{typ})$
- Easy to control gate switching
- Enhancement mode:  $V_{th} = 2.5$  to  $4.5V$
- 100% avalanche tested
- RoHS compliant

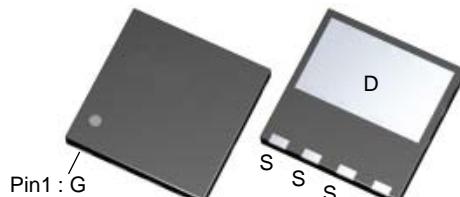
## Key Performance Parameters



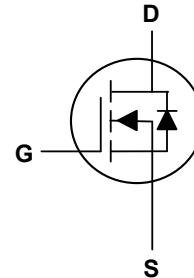
Parameter	Value	Unit
$V_{DS} @ T_{j,\max}$	650	V
$R_{DS(ON),\max}$	65	mΩ
$I_D$	50	A
$Q_{g,\text{typ}}$	75	nC
$I_{DM}$	150	A

## Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger, Lighting



DFN8X8 Top View



## Absolute Maximum Ratings( $T_c=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	650	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Continuous Drain Current <sup>1</sup>	$I_D @ T_c=25^\circ\text{C}$	50	A
Continuous Drain Current <sup>1</sup>	$I_D @ T_c=100^\circ\text{C}$	27	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	150	A
Single Pulse Avalanche Energy <sup>3</sup>	$E_{AS}$	281	mJ
Total Power Dissipation <sup>4</sup>	$P_D$	48	W
Storage Temperature Range	$T_{STG}$	-55 to 150	°C
Operating Junction Temperature Range	$T_J$	-55 to 150	°C

## Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient <sup>1</sup>	$R_{\theta JA}$	---	62.5	°C/W
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	---	2.6	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	650	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$ , $I_D=25\text{A}$	---	53	65	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D = 250\mu\text{A}$	2.5	---	4.5	V
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=650\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 30\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	$\text{nA}$
Gate Resistance	$R_g$	$V_{\text{DS}}=0\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	1.3	---	$\Omega$
Total Gate Charge	$Q_g$	$V_{\text{DS}}=400\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $I_D=25\text{A}$	---	75	---	nC
Gate-Source Charge	$Q_{\text{gs}}$		---	17	---	
Gate-Drain Charge	$Q_{\text{gd}}$		---	34	---	
Turn-On Delay Time	$T_{\text{d}(\text{on})}$	$V_{\text{DS}}=400\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $R_G=10\Omega$ , $I_D=25\text{A}$	---	17	---	ns
Rise Time	$T_r$		---	8	---	
Turn-Off Delay Time	$T_{\text{d}(\text{off})}$		---	71	---	
Fall Time	$T_f$		---	9	---	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=400\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	3208	---	pF
Output Capacitance	$C_{\text{oss}}$		---	81	---	
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	---	---	

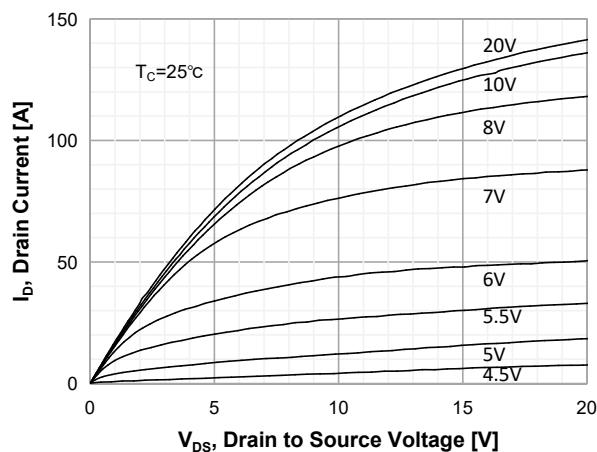
**Drain-Source Diode Characteristics**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage <sup>2</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}$ , $I_S=25\text{A}$ , $T_J=25^\circ\text{C}$	---	---	1.2	V
Reverse recovery time	$t_{\text{rr}}$	$I_F=25\text{A}$ , $dI/F/dt=100\text{A}/\mu\text{s}$	---	413	---	ns
Reverse recovery charge	$Q_{\text{rr}}$		---	7.2	---	nC

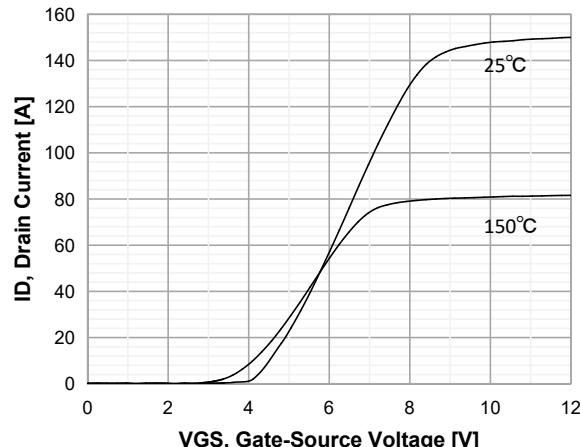
**Note:**

1. Limited by  $T_{j,\text{max}}$ . Maximum Duty Cycle D = 0.50
2. Pulse width  $t_p$  limited by  $T_{j,\text{max}}$
3. Identical low side and high side switch with identical  $R_G$
4.  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ ,  $I_{AS}=6.6\text{A}$ , Starting  $T_J=25^\circ\text{C}$

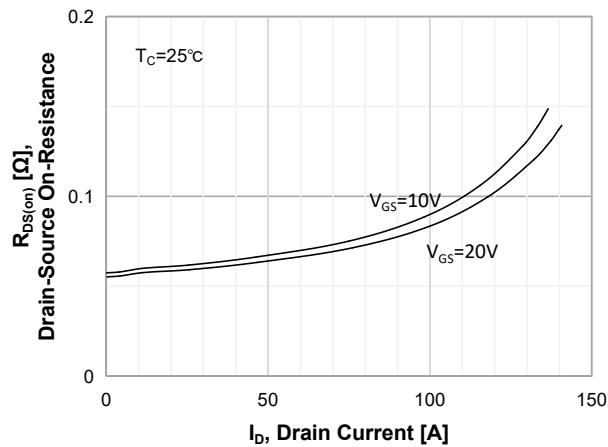
## Typical Characteristics



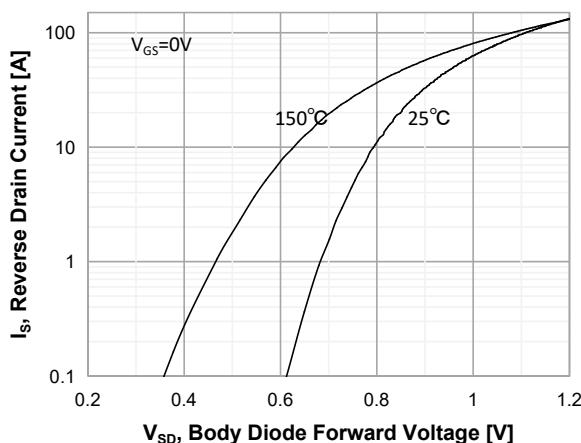
**Figure 1. On-Region Characteristics**



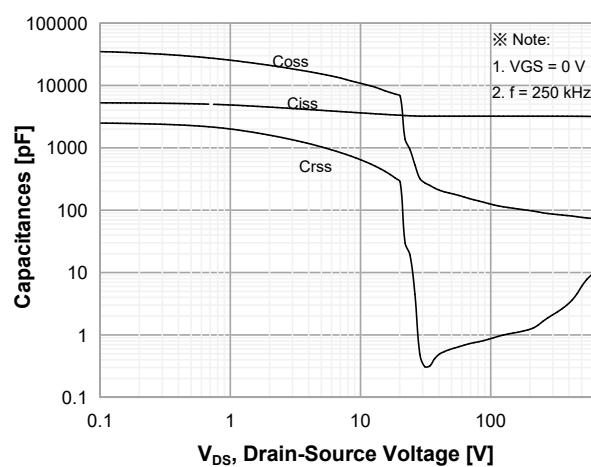
**Figure 2. Transfer Characteristics**



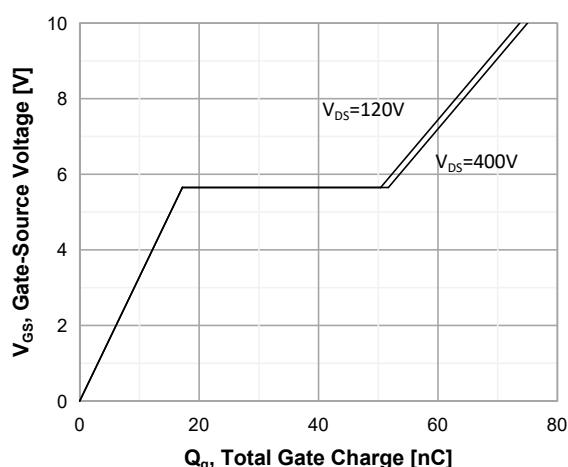
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



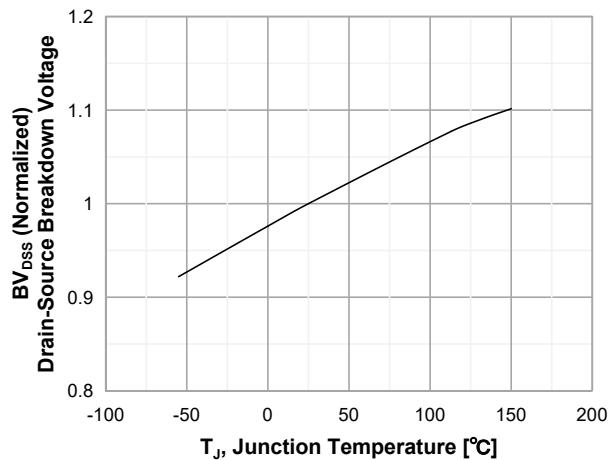
**Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature**



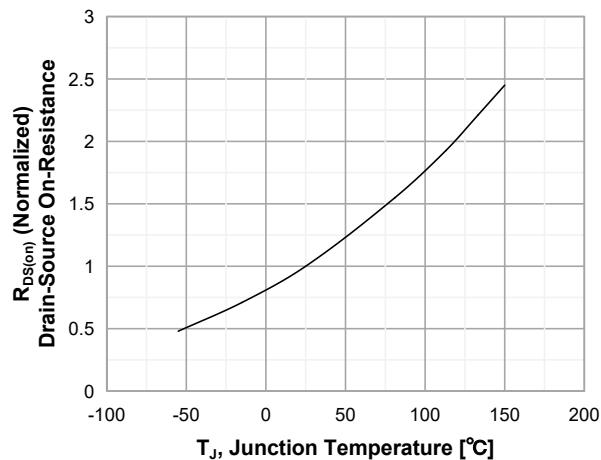
**Figure 5. Capacitance Characteristics**



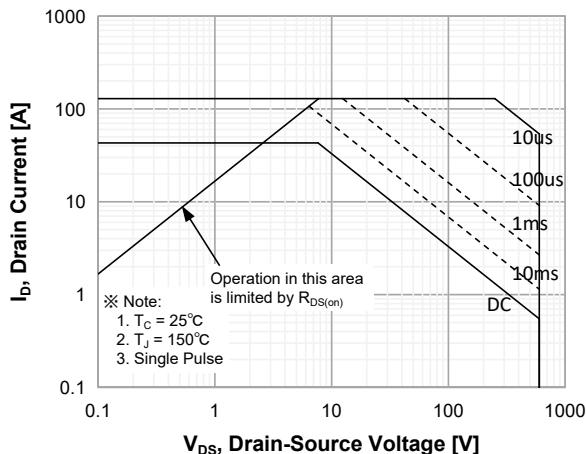
**Figure 6. Gate Charge Characteristics**



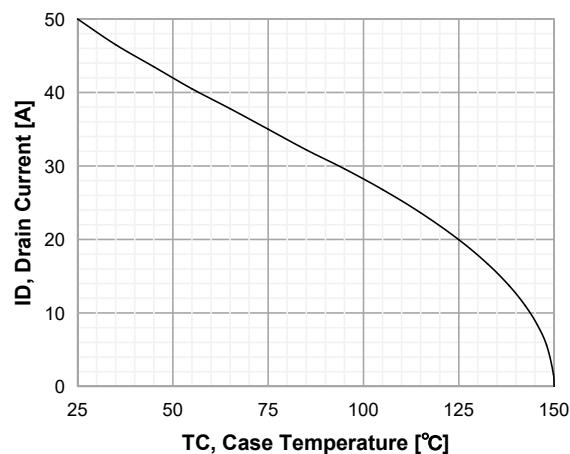
**Figure 7. Breakdown Voltage Variation vs Temperature**



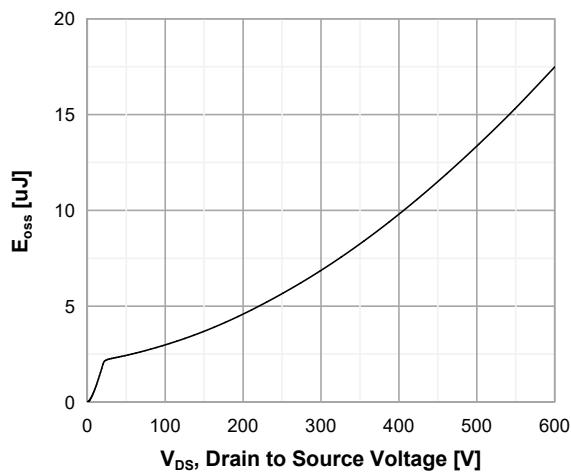
**Figure 8. On-Resistance Variation vs Temperature**



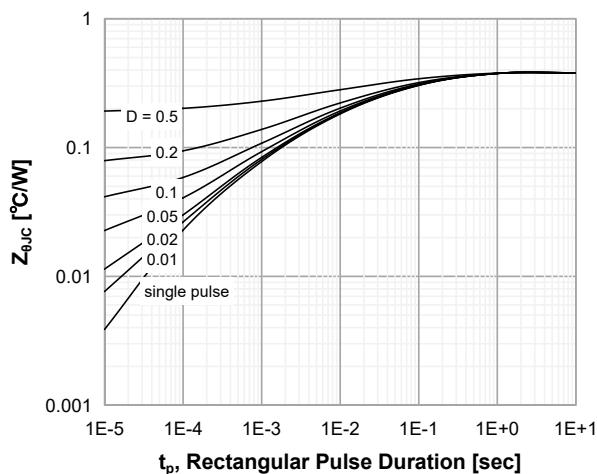
**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**

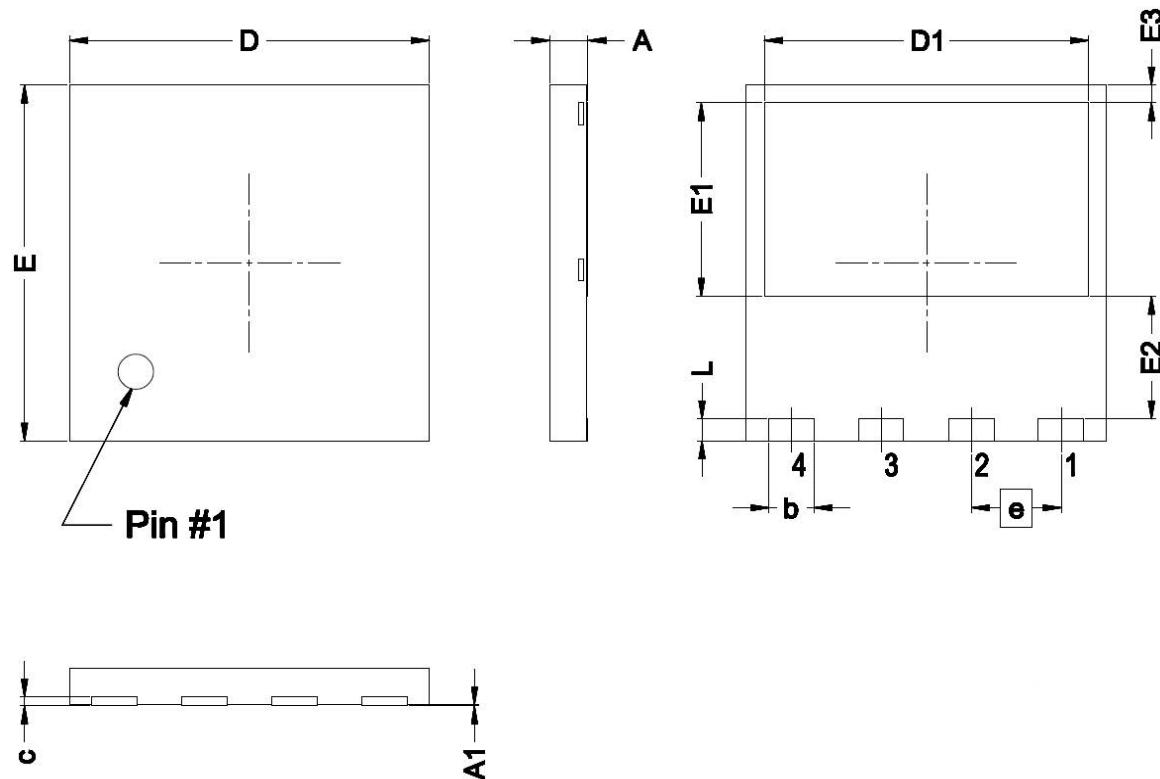


**Figure 11. E<sub>oss</sub> vs. Drain to Source Voltage**



**Figure 12. Transient Thermal Response Curve**

### DFN8X8 Package Outline Dimensions



<b>Symbol</b>	<b>Dimensions (unit:mm)</b>			<b>Symbol</b>	<b>Dimensions (unit:mm)</b>		
	<b>Min</b>	<b>Typ</b>	<b>Max</b>		<b>Min</b>	<b>Typ</b>	<b>Max</b>
<b>A</b>	0.75	0.85	0.95	<b>E</b>	7.90	8.00	8.10
<b>A1</b>	0.00		0.05	<b>E1</b>	4.20	4.35	4.45
<b>b</b>	0.90	1.00	1.10	<b>E2</b>	2.60	2.75	2.85
<b>c</b>	0.10	0.20	0.30	<b>E3</b>	0.30	0.40	0.50
<b>D</b>	7.90	8.00	8.10	<b>e</b>	2.00 BSC		
<b>D1</b>	7.10	7.20	7.30	<b>L</b>	0.40	0.50	0.60



## **Printing Information**

**ATC** =====Brand

**XXXXXXX** =====Material Code

**XXYY** =====XX Representative Year  
YY Representative Weeks